SQJ110EP

AUTOMOTIVE

RoHS

COMPLIANT

HALOGEN FREE

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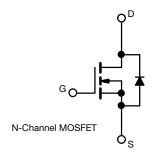
Automotive N-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY 100 V_{DS} (V) $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$ 0.0063 $I_D(A)$ 170 Configuration Single PowerPAK SO-8L Package

FEATURES

- TrenchFET[®] Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION				
Package	PowerPAK SO-8L			
Lead (Pb)-free and halogen-free	SQJ110EP (for detailed order number please see <u>www.vishay.com/doc?79776</u>)			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	100	V	
Gate-source voltage		V _{GS} ± 20		v	
Continuous drain current	T _C = 25 °C	I-	170		
	T _C = 125 °C	I _D	98		
Continuous source current (diode conduction)		I _S	170	А	
Pulsed drain current		I _{DM}	224		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	41		
Single pulse avalanche energy		E _{AS}	84	mJ	
Maximum power dissipation	T _C = 25 °C	PD	500	W	
	T _C = 125 °C	۳D	166	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^b			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^a	R _{thJA}	42	°C/W	
Junction-to-case (drain)		R _{thJC}	0.3	0/10	

Notes

a. When mounted on 1" square PCB (FR4 material)

b. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•	•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		100	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		2.7	3.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		V _{GS} = 0 V V _{DS} = 100 V -		-	-	10	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.005	0.0063	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0130	Ω
		$V_{GS} = 10 V$	I _D = 15 A, T _J = 175 °C	-	-	0.0166	
Forward transconductance b	g _{fs}	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$		-	130	-	S
Dynamic ^b	•	-				•	1
Input capacitance	Ciss		V _{DS} = 25 V, f = 1 MHz	-	4357	6100	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	473	663	
Reverse transfer capacitance	C _{rss}				30	42	
Total gate charge ^c	Qg			-	75	113	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	V _{GS} = 10 V V _{DS} = 50 V, I _D = 15 A		20	-	nC
Gate-drain charge ^c	Q _{gd}			-	15	-	
Gate resistance	Rg	f = 1 MHz		0.5	0.9	1.40	Ω
Turn-on delay time ^c	t _{d(on)}		$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 3.33 \Omega$		16	24	ns
Rise time ^c	t _r	V _{DD} =			5	9	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 15$ A, $V_{GEN} = 10$ V, $R_g = 1$ Ω		-	36	54	
Fall time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Chara	acteristics ^b	•			•	•	
Pulsed current ^a	I _{SM}			-	-	224	Α
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	48	96	ns
Body diode reverse recovery charge	Q _{rr}			-	83	166	nC
Reverse recovery fall time	t _a			-	33	-	ns
Reverse recovery rise time	t _b			-	15	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	3.0	-	А

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

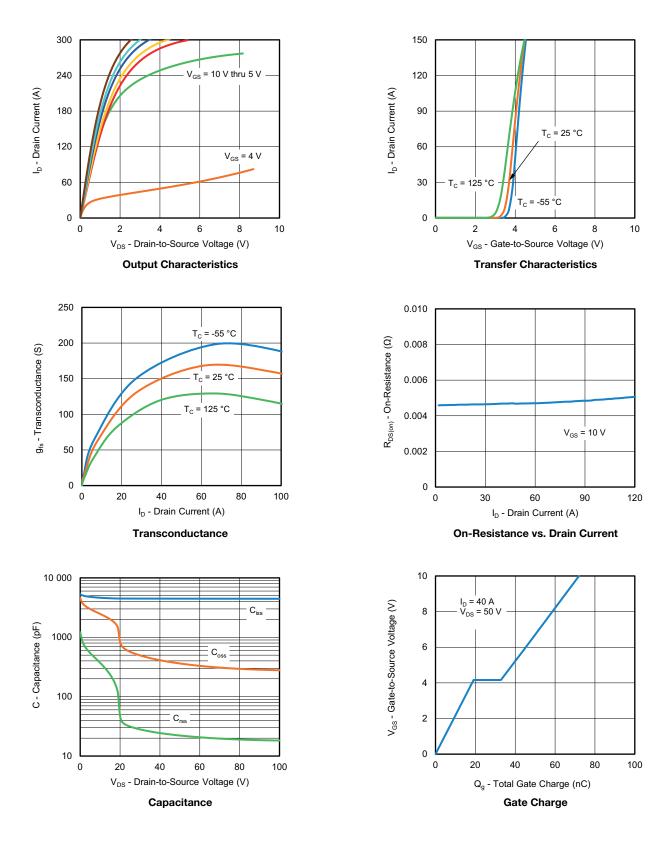
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



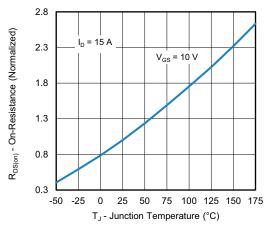
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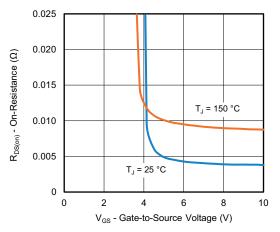


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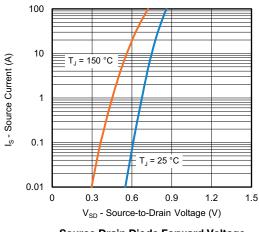
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



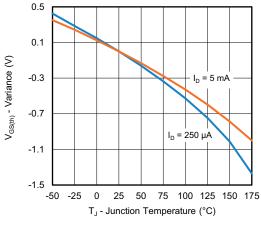
On-Resistance vs. Junction Temperature



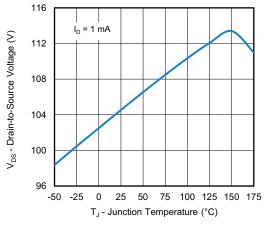
On-Resistance vs. Gate-to Source Voltage



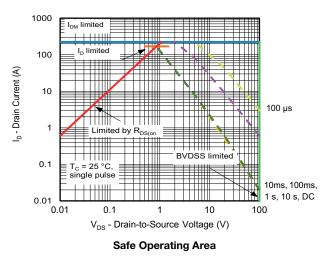
Source Drain Diode Forward Voltage Note



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



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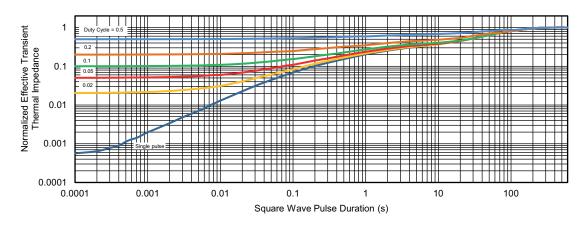
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a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

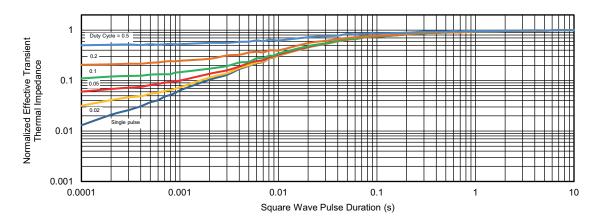


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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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